

Appl. No. 09/488,973

A marked up version showing amendments to any claims being changed is provided in one or more accompanying pages separate from this amendment in accordance with 37 C.F.R. § 1.121(c)(1)(ii). Any claim not accompanied by a marked up version has not been changed relative to the immediate prior version, except that marked up versions are not being supplied for any added claim or canceled claim.

Cancel claims 1-9 and 18.

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10. (amended) A method of bonding a physical vapor deposition target material to a backing plate material, comprising:

joining the target material and backing plate material in physical contact with one another, the backing plate and target material both predominately comprising aluminum; and

thermally treating the joined target and backing plate materials to simultaneously diffusion bond the target material to the backing plate material and develop grains in the target material, the diffusion bonding comprising solid state diffusion between the backing plate and target materials, a predominate portion of the developed grains having a maximum dimension of less than 100 microns.